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UGC-Junior Research Fellow,  
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### **Educational Qualifications:**

UGC-Senior Research Fellow (Dec, 2024 – Till date): Department of Electronic Science, University of Calcutta, Kolkata, India.

UGC-Junior Research Fellow (Nov, 2022 – Nov, 2024): Department of Electronic Science, University of Calcutta, Kolkata, India.

Project Assistant (Nov, 2021- Nov, 2022): Department of Electronic Science, University of Calcutta, Kolkata, India.

M. Sc. Physics (2019-2021); Rajabazar Science College, University of Calcutta, Kolkata, India.  
*Specialization: Solid State Electronics, Quantum Electronics, Microwave.*

B. Sc. Physics (2016-2019); St. Xavier's College (Autonomous), Kolkata, India.

### **Present Status:**

1. Presently working on modeling the transport phenomena of single and multi-quantum dot systems in gated nanowire FETs, using Non-Equilibrium Green's Function (NEGF) formalism, for quantum computing and next generation electronics devices.
2. Growth of composite oxide thin films by low-temperature VLS technique and their electrical/physical characterization.

### **Skills:**

- Experienced in Python and MATLAB for scientific computing.
- Experience with working in class-100 clean room.
- Have work experience in operating Scanning Electron Microscope (Zeiss Auriga), EBSD (Oxford Instruments) and electron-beam lithography (Raith Elphy Plus).
- Experienced in operating thermal deposition system for thin film deposition.

- Experience in semiconductor device characterization (C-V, I-V and four probe resistivity measurements, including low temperature characterization (Ecopia)).
- Developed custom Hall effect/resistivity measurement setup for room temperature measurements.
- Material characterization using Spectroscopic Ellipsometry (Sentech SE850) and absorption spectroscopy (Perkin Elmer λ-1050).

### **Book Chapters:**

1. **Nilayan Paul**, Basudev Nag Chowdhury, Sanatan Chattopadhyay. *Investigating the Impact of Ge-Quantum Well Width in Si/SiO<sub>2</sub>/Ge/SiO<sub>2</sub>/Pt Resonant Tunneling Device with NEGF Formalism*. In: Giri, C., Iizuka, T., Rahaman, H., Bhattacharya, B.B. (eds) **Emerging Electronic Devices, Circuits and Systems**. Lecture Notes in Electrical Engineering, vol 1004. Springer (2023).  
DOI: [https://doi.org/10.1007/978-981-99-0055-8\\_20](https://doi.org/10.1007/978-981-99-0055-8_20)

### **Publications in Peer Reviewed International Journals:**

1. **Nilayan Paul**, S. Chattopadhyay. *Understanding the Nanowire Material-Dependent Charge Qubit Performance of Voltage-Tunable Double Quantum Dot Gate Nanowire Channel Field-Effect Transistors (DQD-NWFETs)*. Journal of Electronic Materials, 54, pp. 9511 – 9523 (2025). (IF 2.5)  
DOI: <https://doi.org/10.1007/s11664-025-12059-3>
2. **Nilayan Paul**, S. Chattopadhyay. *Design and modeling of resonant tunneling transport-controlled voltage-induced double quantum dot channel nanowire field-effect-transistor (DQD-FET) for multi-threshold current levels*. Solid-State Electronics, 230, p. 109259 (2025). (IF 1.4)  
DOI: <https://doi.org/10.1016/j.sse.2025.109259>
3. A. Mukherjee, A. Bhattacharya, **N. Paul**, A. Tiwari, S. Kanungo, S. Chattopadhyay. *Exploring the Ga-doping dependent optical transparency and electrical conductivity of thermally evaporated p-type ZnO films*. Journal of Materials Science: Materials in Electronics, 36, p. 2304 (2025). (IF 2.8)  
DOI: <https://doi.org/10.1007/s10854-025-16334-1>

### **Publications in Peer Reviewed International Conferences /Symposia /Workshops:**

1. **Nilayan Paul**, Basudev Nag Chowdhury, Sanatan Chattopadhyay. *Investigating the impact of Ge-quantum well width in Si/SiO<sub>2</sub>/Ge/SiO<sub>2</sub>/Pt resonant tunneling device with NEGF formalism*, 5<sup>th</sup> International Symposium on Devices, Circuits and Systems (ISDCS), 2022.
2. **Nilayan Paul**, Basudev Nag Chowdhury, Sanatan Chattopadhyay. *Understanding the composition dependent charge qubit operations in a dual-gate Al<sub>x</sub>Ga<sub>1-x</sub>As nanowire FET using NEGF approach*, XXII International Workshop on Physics of Semiconductor Devices (IWPSD), 2023.
3. **Nilayan Paul**, Sanatan Chattopadhyay. *Understanding the material dependent charge qubit performance of voltage-tunable double quantum channel nanowire FETs*. 2<sup>nd</sup> International Conference on Low Energy Devices (ICLED), 2024.

4. **Nilayan Paul**, Sanatan Chattopadhyay. *Understanding the transport of voltage-induced quantum dots in nanowire channel field-effect-transistors.* 1<sup>st</sup> International Conference on Sustainable Technologies (ICST), 2024.

**Preprints:**

1. **Nilayan Paul**, Basudev Nag Chowdhury, Sanatan Chattopadhyay. *Design aspects of dual gate GaAs nanowire FET for room temperature charge qubit operation: A study on diameter and gate engineering.* (preprint: <https://doi.org/10.48550/arXiv.2304.10554>)

**Awards:**

- UGC Junior Research Fellowship, 2022.
- Best presentation award, ICLED-2024.